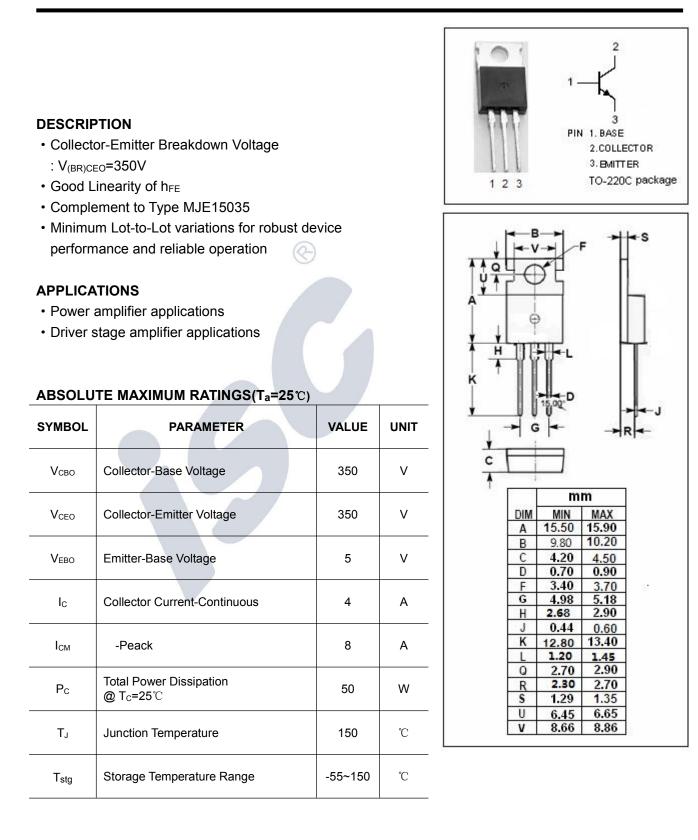


INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

MJE15034



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MJE15034

ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I _C =10mA ; I _B = 0	350			V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 0.1A			0.5	V
V _{BE} (on)	Base-Emitter On Voltage	I _C =1A ; V _{CE} = 5V			1.0	V
Ісво	Collector Cutoff Current	V _{CB} = 350V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} =5V; I _C = 0			1.0	μA
h_{FE1}	DC Current Gain	I _C =0.1A ; V _{CE} =5V	100			
h _{FE2}	DC Current Gain	I _C =0.5A ; V _{CE} =5V	100			
h _{FE3}	DC Current Gain	I _C =1.0A ; V _{CE} =5V	50			
h _{FE4}	DC Current Gain	Ic=2.0A ; V _{CE} =5V	10			
f⊤	Current-Gain—Bandwidth Product	I _C =0.1A;V _{CE} =10V		15		MHz

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